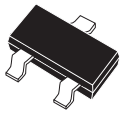
CMPT6428
CMPT6429

NPN SILICON TRANSISTOR



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT6428, CMPT6429 types are NPN Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high gain amplifier applications.
Marking Codes are C1K and C1L Respectively.

MAXIMUM RATINGS (T_A=25°C)

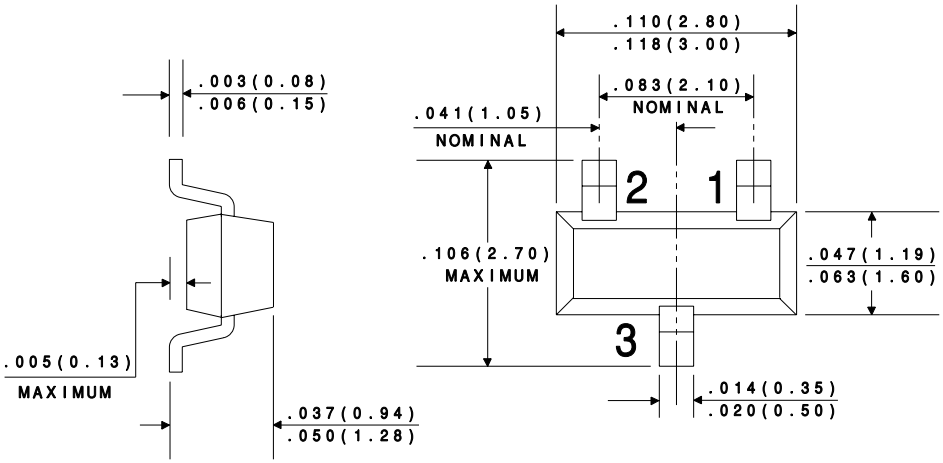
	SYMBOL	CMPT6428	CMPT6429	UNITS
Collector-Base Voltage	V_{CBO}	60	55	V
Collector-Emitter Voltage	V_{CEO}	50	45	V
Emitter-Base Voltage	V_{EBO}	6.0		V
Collector Current	I_C	200		mA
Power Dissipation	P_D	350		mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150		°C
Thermal Resistance	Θ_{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		CMPT6428		CMPT6429		
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=30V		10		10	nA
I_{CEO}	V_{CE}=30V		100		100	nA
I_{EBO}	V_{BE}=5.0V		10		10	nA
BV_{CBO}	I_C=100μA		60		55	V
BV_{CEO}	I_C=1.0mA		50		45	V
$V_{CE(SAT)}$	I_C=10mA, I_B=0.5mA		0.20		0.20	V
$V_{CE(SAT)}$	I_C=100mA, I_B=5.0mA		0.60		0.60	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=1.0mA	0.56	0.66	0.56	0.66	V
h_{FE}	V_{CE}=5.0V, I_C=10μA	250		500		
h_{FE}	V_{CE}=5.0V, I_C=100μA	250	650	500	1250	
h_{FE}	V_{CE}=5.0V, I_C=1.0mA	250		500		
h_{FE}	V_{CE}=5.0V, I_C=10mA	250		500		
f_T	V_{CE}=5.0V, I_C=1.0mA, f=100MHz	100	700	100	700	MHz

SYMBOL	TEST CONDITIONS	CMPT6428 MIN	CMPT6428 MAX	CMPT6429 MIN	CMPT6429 MAX	UNITS
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		3.0		3.0	pF
C_{ib}	V_{BE}=0.5V, I_C=0, f=1.0MHz		8.0		8.0	pF

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR

R2

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